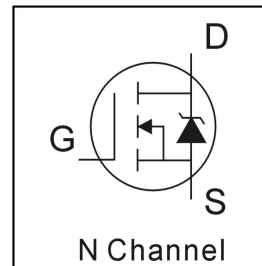


**N Channel Power MOSFET with low RDS(ON)**

**Chip Specification**

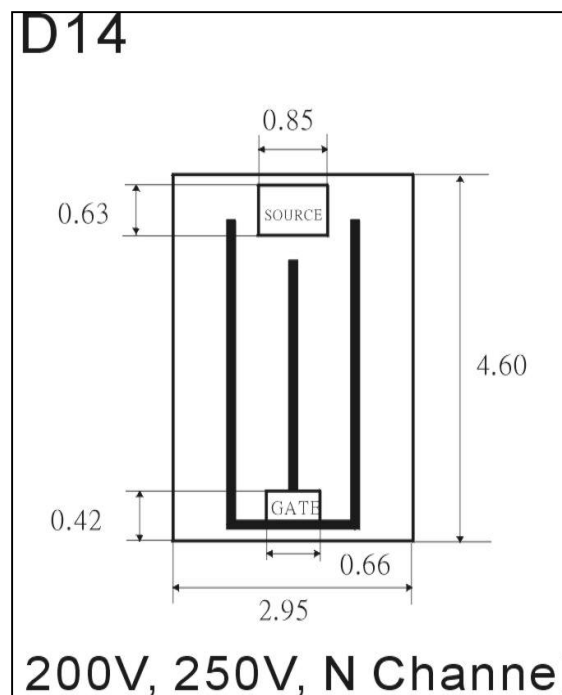
**General Description:**

- \* Advanced Process Technology
- \* Dynamic dV/dt Rating
- \* **175°C Operating Temperature**
- \* **Fast Switching**
- \* **Fully Avalanche Rated**
- \* **low RDS(ON)**



**Mechanical Data:**

<b>D14</b>	
Dimension	<b>2.95mm x4.6mm</b>
Thickness:	<b>400 μm</b>
Metallization:	
Top :	<b>Al</b>
Backside :	<b>CrNiAg / Au</b>
Suggested Bonding Conditions:	
Die Mounting:	<b>Solder Perform</b>
<b>95/5 PbSn or 92.5./2.5/5 PbAgIn</b>	
Source Bonding Wire:	<b>8 mil Al</b>



**Absolute Maximum Rating**

@Ta=25°C

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	250	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	0.45	Ω	VGS=10V, ID=4.05A
Continuous Drain current ( in target package)	ID@25°C	8.1	A	VGS=10V
Continuous Drain current ( in target package)	ID@100°C	5.1	A	VGS=10V
Operation Junction	Tj	-55~175	°C	
Storage Temperature	TSTR	-55~175	°C	

**Target Device: IRFP634**

TO-220AB

PD

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W

@Tc=25°C

